



B.E/B.TECH DEGREE EXAMINATIONS: NOV/DEC 2023

(Regulation 2018)

Sixth Semester

ELECTRONICS AND COMMUNICATION ENGINEERING

U18ECI6203T: VLSI and HDL Programming

COURSE OUTCOMES

CO1: Implement and verify combinational and sequential circuits using Verilog HDL.

CO2: Explain working and electrical properties of MOSFET.

CO3: Discuss the CMOS fabrication Technologies.

CO4: Apply CMOS logics in complex digital circuits.

CO5: Discuss various implementation strategies.

Time: Three Hours

Maximum Marks: 100

Answer all the Questions: -

PART A (10 x 2 = 20 Marks)

(Answer not more than 40 words)

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|--|-----|-------------------|
| 1. In the order of least to highest level of abstraction, list the various modeling types used in Verilog HDL | CO1 | [K ₁] |
| 2. Distinguish Continuous assignment statement from Procedural assignment statement. | CO1 | [K ₂] |
| 3. Justify the statement and state whether it's true or false with necessary justification - A pass transistor can drive more than one transistor without any degradation. | CO4 | [K ₂] |
| 4. Define the effect of velocity saturation in short channel transistors | CO2 | [K ₁] |
| 5. Name any two specific applications of FPGA. | CO5 | [K ₁] |
| 6. Using pass transistors, model an AND logic. | CO4 | [K ₃] |
| 7. List any four ideal characteristics of CMOS Inverter. | CO2 | [K ₁] |
| 8. Which method of CMOS Fabrication completely neglects latch up effects? How? | CO3 | [K ₂] |
| 9. Rephrase the significance of demarcation line in stick diagrams. | CO3 | [K ₂] |
| 10. Recall any two advantages of SoC. | CO5 | [K ₁] |

Answer any FIVE Questions:-

PART B (5 x 16 = 80 Marks)

(Answer not more than 400 words)

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|--|---|-----|-------------------|
| 11. a) Explain the steps involved in the fabrication of CMOS using N well methodology with necessary diagrams. | 8 | CO3 | [K ₂] |
| b) Make use of CMOS Design rules and model a NOR gate using static CMOS | 8 | CO3 | [K ₃] |

Logic with its stick diagram and layout.

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|-----|----|--|----|-----|-------------------|
| 12. | a) | Deduce the drain current equation for an enhancement mode N-type MOSFET with necessary V-I plots. | 8 | CO2 | [K ₂] |
| | b) | Explain the working of a CMOS Inverter specifying the five regions of operation with S curve. | 8 | CO2 | [K ₂] |
| 13. | a) | Design an 8x3 Encoder using behavioral modeling, in Verilog HDL | 8 | CO1 | [K ₃] |
| | b) | Construct a Verilog code to implement a arithmetic logic unit that performs eight different functions. | 8 | CO1 | [K ₃] |
| 14. | a) | Outline the principle and working of Field Programmable Gate Array with its subcomponents in detail. | 8 | CO5 | [K ₂] |
| | b) | Explain the SoC design flow with a neat diagram. | 8 | CO5 | [K ₂] |
| 15. | a) | Adapt the Boolean expression $F = AB+CD$ using the following logic design styles
i) Domino logic
ii) Static CMOS Logic
iii) Pseudo NMOS logic | 8 | CO4 | [K ₃] |
| | b) | Interpret and appraise the logic design style that helps in overcoming errors due to race conditions. | | CO4 | [K ₂] |
| 16. | a) | Elaborate every step of VLSI Design flow with a neat diagram. | 10 | CO1 | [K ₂] |
| | b) | Compare Enhancement and Depletion mode MOSFETs. | 6 | CO2 | [K ₂] |
